

Marking Information

Site 1



FZ = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Е		Н		J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	4	_	1	4	E	c	7	0	0	^	N.I.	_

Site 2



FZ = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Date Code Key												
Year	2017		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	7		0	1	2	3	4	5	6	7	8	9
Week	1-26			27-52			53					
Code		A	∖-Z		a-z				Z			
Internal Code	Sun	ı	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	V	Х		Υ		Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-12	V		
Gate-Source Voltage	V _{GSS}	±8	V		
Continuous Drain Current V _{GS} = -4.5V (Note 6)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	lo	-11 -8.7	А
Continuous Diain Current VGS = -4.5V (Note 6)	t<5s	$T_A = +25$ °C $T_A = +70$ °C	lο	-15 -12	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I_{DM}	-70	Α		
Maximum Body Diode Continuous Current (Note 6)	Is	-2.5	Α		
Avalanche Current (Note 7) L = 0.1mH	las	-24	Α		
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	31	mJ		

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.8	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	152	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<5s	$R_{\theta JA}$	81	C/VV	
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.0	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	р	63	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<5s	$R_{\theta JA}$	34		
Thermal Resistance, Junction to Case (Note 6)	Steady State	RθJC	15		
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	-12	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-100	nA	$V_{DS} = -9.6V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH)	-0.3	_	-1.0	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
			8.3	11		$V_{GS} = -4.5V, I_{D} = -5A$	
Static Drain-Source On-Resistance	Process		9	14	mΩ	$V_{GS} = -3.7V, I_{D} = -5A$	
Static Diain-Source On-Resistance	RDS(ON)	-	12	19	11122	Vgs = -2.5V, ID = -4A	
			16	30		V _G S = -1.8V, I _D = -1A	
Diode Forward Voltage	Vsp	_	-0.8	-1.2	V	Vgs = 0V, Is = -10A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	1860		pF	101/11/101/	
Output Capacitance	Coss	_	498			$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	416	_		1 = 1.000112	
Gate Resistance	Rg	_	11	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	26	_			
Total Gate Charge (V _{GS} = -8V)	Qg	_	44	_		\/ C\/	
Gate-Source Charge	Qgs	_	3.3	_	nC	$V_{DS} = -6V, I_{D} = -10A$	
Gate-Drain Charge	Q _{gd}	_	8.1	_			
Turn-On Delay Time	t _D (ON)	_	7.0	_			
Turn-On Rise Time	t _R	_	10.6	_		$V_{DS} = -6V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	62.2	_	ns	$R_G = 1\Omega$, $I_D = -8A$	
Turn-Off Fall Time	tF	_	61				
Reverse Recovery Time	trr	_	34.4	_	ns	100 11/11 5000/	
Reverse Recovery Charge	Q _{RR}	_	28.1		nC	I _F = -12A, di/dt = 500A/μs	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

^{7.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.



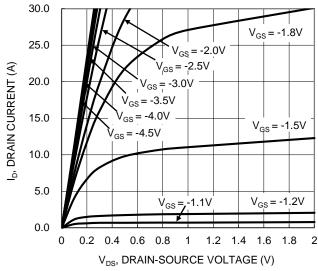


Figure 1. Typical Output Characteristic

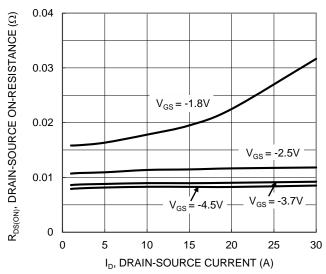


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

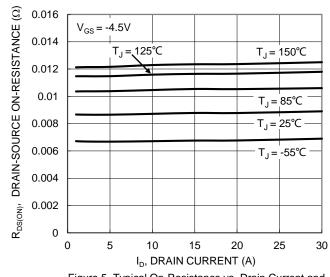


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

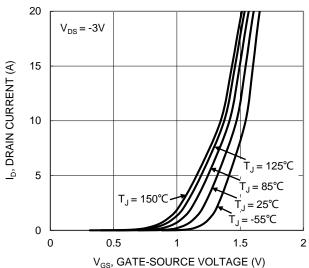


Figure 2. Typical Transfer Characteristic

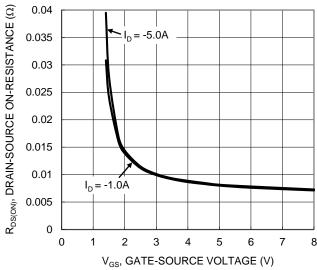


Figure 4. Typical Transfer Characteristic

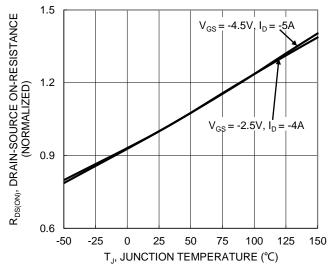


Figure 6. On-Resistance Variation with Temperature



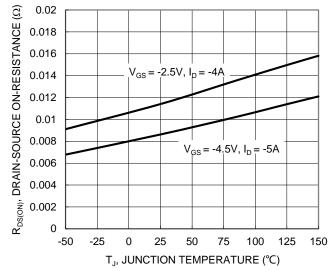


Figure 7. On-Resistance Variation with Temperature

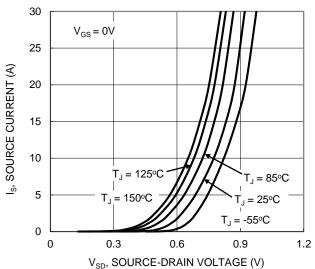


Figure 9. Diode Forward Voltage vs. Current

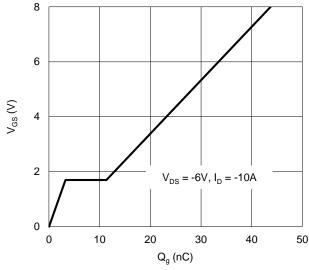


Figure 11. Gate Charge

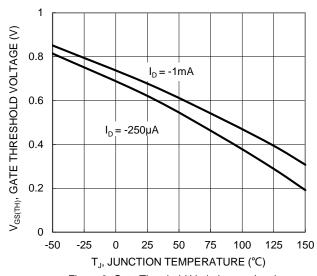


Figure 8. Gate Threshold Variation vs. Junciton Temperature

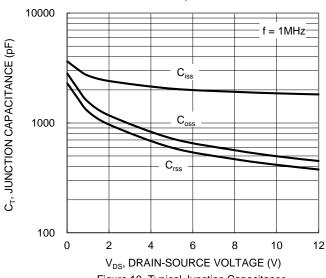


Figure 10. Typical Junction Capacitance

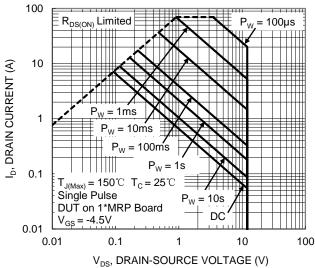


Figure 12. SOA, Safe Operation Area



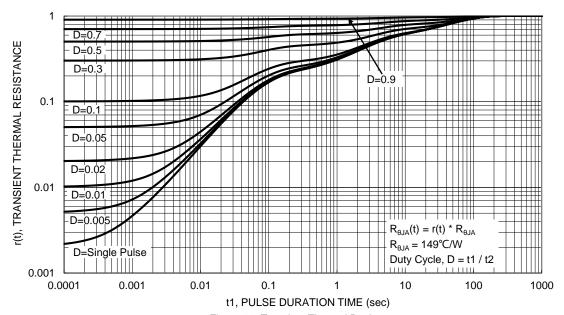


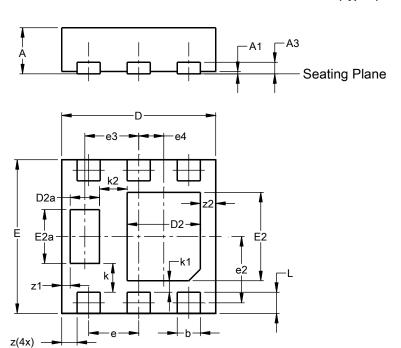
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

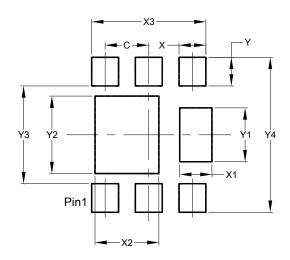


U-DFN2020-6								
(Type F)								
Dim	Min Max Typ							
Α	0.57	0.63	0.60					
A1	0.00	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.43	0.38					
E	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E2a	0.65	0.75	0.70					
е	0.65 BSC							
e2	0.863 BSC							
е3		0.70 BS	С					
e4	().325 BS	SC					
k		0.37 BS						
k1	0.15 BSC							
k2	0.36 BSC							
L		0.325						
Z		0.20 BS	_					
z 1	().110 BS	SC					
z2		0.20 BS	С					
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)				
С	0.650				
Х	0.400				
X1	0.480				
X2	0.950				
Х3	1.700				
Υ	0.425				
Y1	0.800				
Y2	1.150				
Y3	1.450				
Y4	2.300				



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